MITSUBISHI SEMICONDUCTOR (GaAs FET)

MGF0907B

L, S BAND POWER GaAs FET

DESCRIPTION

The MGF0907B, GaAs FET with an N-channel schottky gate, is designed for use in UHF band amplifiers.

FEATURES

- Class A operation
- High output power

P_{1dB}=40dBm (TYP) @2.3 GHz

• High power gain

GLP=10 dB (TYP) @2.3GHz

- High power added efficiency
 - $\eta_{add} = 37\%$ (TYP) @2.3GHz, P_{1dB}
- Hermetically sealed metal-ceramic package with ceramic lid

APPLICATION

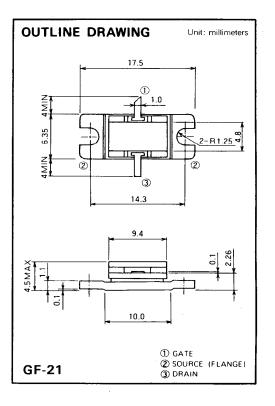
UHF band power amplifiers.

QUALITY GRADE

IG

RECOMMENDIND BIAS CONDITIONS

- V_{DS}=10V
- I_D=2.4A
- Rg = 50 Ω
- Refer to Bias Procedure



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter	Ratings	Unit
V _{GDO}	Gate to drain voltage	- 15	٧
V _{GSO}	Gate to source voltage	- 15	٧
ID	Drain current	6	А
I _{GR}	Reverse-gate current	-20	mΑ
1 _{GF}	Forward gate current	+ 42	mA
PT	Total power dissipation *1	37.5	w
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65~+175	°C

^{*1:} T_C = 25°C

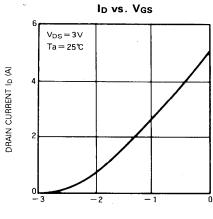
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

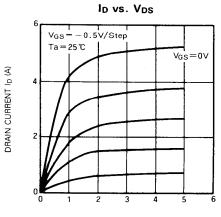
		Limits				
Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
Ioss	Saturated drain current	V _{DS} =3V, V _{GS} =0V	_	4.0	6.0	Α
9 _m	Transconductance	V _{DS} =3V, t _D =2.2A	_	2.0		8
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} =3V, I _D =20mA	- 1	-2.5	-4	V
P _{1dB}	Output power at 1dB gain compression		38.5	40		dBm
GLP	Linear power gain	$V_{DS} = 10V, I_{D} = 2.4A, f = 2.3GHz$	8	10	_	dB
ID	Drain current	VBS = 10V, 1D = 2.4M, 1= 2.30112	_	2.2	3.0	А
$\eta_{\sf add}$	Power added efficiency at P _{1dB}		_	37	_	%
Rth(ch-c)	Thermal resistance * 1	ΔV_f method	-	_	4.0	°C/W

^{*1.} Channel to case



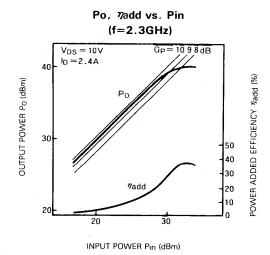
TYPICAL CHARACTERISTICS

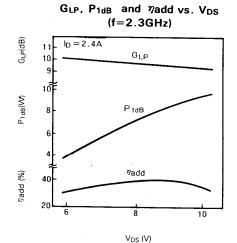




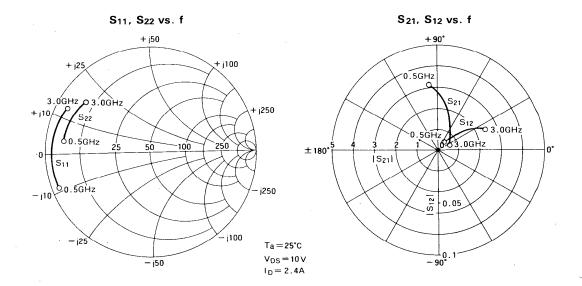
GATE TO SOURCE VOLTAGE V_{GS} (V)







L, S BAND POWER GaAs FET



S PARAMETERS (Ta=25 °C, V_{DS} =10V, I_{D} =2.4A)

f (GHz) Ma	S	S ₁₁		S ₂₁		S ₁₂		S ₂₂		MAG
	Magn.	Ang. (deg)	Magn	Ang. (deg)	Magň.	Ang. (deg)	Magn.	Ang. (deg)	К	(dB)
0.5	0.947	- 162.1	3.089	96.7	0.010	45.8	0.823	171.6	1.086	23.1
0.6	0.943	- 165.6	2.793	90.8	0.012	44.1	0.822	170.1	1.055	22.2
0.7	0.939	- 168.7	2.524	85.5	0.014	42.7	0.822	168.7	1.038	21.4
0.8	0.936	- 171.4	2.281	80.7	0.014	41.5	0.821	167.5	1.024	20.6
0.9	0.934	-173.8	2.092	76.4	0.017	40.5	0.821	166.4	1.043	19.6
1.0	0.932	- 175.9	1.865	72.7	0.018	39.7	0.820	165.5	1.072	18.5
1.1	0.931	- 177.7	1.691	69.3	0,.019	39.0	0.819	164.7	1.095	17.6
1.2	0.930	- 179.3	1.537	66.4	0.020	38.4	0.818	164.0	1.124	16.7
1.3	0.929	179.3	1.401	63.7	0.021	37.9	0.817	163.3	1.157	15.8
1.4	0.929	178.1	1.284	61.4	0.021	37.5	0.816	162.7	1.219	15.0
1.5	0.928	177.0	1.183	59.3	0.022	. 37.2	0.815	162.1	1.257	14.3
1.6	0.928	176.0	1.096	57.4	0.022	36.9	0.813	161.5	1.328	13.6
1.7	0.927	175.1	1.024	55.6	0.023	36.6	0.811	160.8	1.367	12.7
1.8	0.927	174.2	0.964	54.0	0.023	36.3	0.810	160.2	1.430	12.3
1.9	0.926	173.3	0.915	52.4	0.024	35.9	0.808	159.4	1.461	11.8
2.0	0.925	172.3	0.875	50.9	0.025	35.5	0.806	158.6	1.488	11.3
2.1	0.923	171.2	0.844	49.3	0.026	35.0	0.803	157.7	1.527	10.8
2.2	0.921	170.0	0.820	47.6	0.027	34.4	0.801	156.7	1.555	10.4
2.3	0.919	168.6	0.801	45.8	0.028	33.7	0.798	155.5	1.584	10.1
2.4	0.916	167.1	0.787	43.9	0.030	32.8	0.769	154.1	1.574	9.7
2.5	0.912	165.3	0.776	41.7	0.032	31.8	0.792	152.6	1.587	9.4
2.6	0.907	163.3	0.767	39.2	0.035	30.6	0.789	150.9	1.570	9.0
2.7	0.902	160.9	0.757	36.5	0.037	29.1	0.786	148.9	1.594	8.6
2.8	0.895	158.3	0.746	33.4	0.040	27.4	0.782	146.6	1.614	8.1
2.9	0.887	155.2	0.735	29.9	0.044	25.4	0.778	144.1	1.620	7.6
3.0	0.879	151.7	0.719	26.0	0.048	23.1	0.774	141.4	1.636	7.1



MGF0907B

L, S BAND POWER GaAs FET

Requests Regarding Safety Designs

Mitsubishi Electric constantly strives to raise the level of its quality and reliability. Despite these concerted efforts, however, there will be occasions when our semiconductor products suffer breakdowns, malfunctions or other problems. In view of this reality, it is requested that every feasible precaution be taken in the pursuit of redundancy design, malfunction prevention design and other safety-related designs, to prevent breakdowns or malfunctions in our products from resulting in accidents involving people, fires, social losses or other problems, thereby upholding the highest levels of safety in the products when in use by customers.

Matters of Importance when Using these Materials

- 1. These materials are designed as reference materials to ensure that all customers purchase Mitsubishi Electric semiconductors best suited to their specific use applications. Please be aware, however, that the technical information contained in these materials does not comprise consent for the execution or use of intellectual property rights or other rights owned by Mitsubishi Electric Corporation.
- 2. Mitsubishi Electric does not assume responsibility for damages resulting from the use of product data, graphs, charts, programs, algorithms or other applied circuit examples described in these materials, or for the infringement of the rights of third-party owners resulting from such use.
- 3. The data, graphs, charts, programs, algorithms and all other information described in these materials were current at the issue of these materials, with Mitsubishi Electric reserving the right to make any necessary updates or changes in the products or specifications in these materials without prior notice. Before purchasing Mitsubishi Electric semiconductor products, therefore, please obtain the latest available information from Mitsubishi Electric directly or an authorized dealer.
- 4. Every possible effort has been made to ensure that the information described in these materials is fully accurate. However, Mitsubishi Electric assumes no responsibility for damages resulting from inaccuracies occurring within these materials.
- 5. When using the product data, technical contents indicated on the graphs, charts, programs or algorithms described in these materials, assessments should not be limited to only the technical contents, programs and algorithm units. Rather, it is requested that ample evaluations be made of each individual system as a whole, with the customer assuming full responsibility for decisions on the propriety of application. Mitsubishi Electric does not accept responsibility for the propriety of application.
- 6. The products described in these materials, with the exception of special mention concerning use and reliability, have been designed and manufactured with the purpose of use in general electronic machinery. Accordingly these products have not been designed and manufactured with the purpose of application in machinery or systems that will be used under conditions that can affect human life, or in machinery or systems used in social infrastructure that demand a particularly high degree of reliability. When considering the use of the products described in these materials in transportation machinery (automobiles, trains, vessels), for objectives related to medical treatment, aerospace, nuclear power control, submarine repeaters or systems or other specialized applications, please consult with Mitsubishi Electric directly or an authorized dealer.
- 7. When considering use of products for purposes other than the specific applications described in these materials, please inquire at Mitsubishi Electric or an authorized dealer.
- 8. The prior consent of Mitsubishi Electric in writing is required for any reprinting or reproduction of these materials.
- 9. Please direct any inquiries regarding further details of these materials, or any other comments or matters of attention, to Mitsubishi Electric or an authorized dealer.

